

75A, 55V, 0.012 Ohm, N-Channel UltraFET Power MOSFETs



These N-Channel power MOSFETs are manufactured using the innovative UltraFET® process. This advanced process technology

achieves the lowest possible on-resistance per silicon area, resulting in outstanding performance. This device is capable of withstanding high energy in the avalanche mode and the diode exhibits very low reverse recovery time and stored charge. It was designed for use in applications where power efficiency is important, such as switching regulators, switching converters, motor drivers, relay drivers, low-voltage bus switches, and power management in portable and battery-operated products.

Formerly developmental type TA75339.

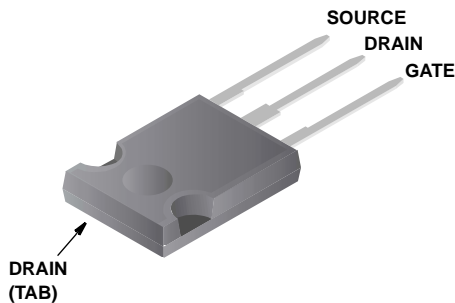
Ordering Information

PART NUMBER	PACKAGE	BRAND
HUF75339G3	TO-247	75339G
HUF75339P3	TO-220AB	75339P
HUF75339S3S	TO-263AB	75339S

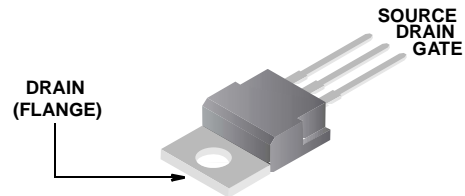
NOTE: When ordering, use the entire part number. Add the suffix T to obtain the TO-263AB variant in tape and reel, e.g., HUF75339S3ST.

Packaging

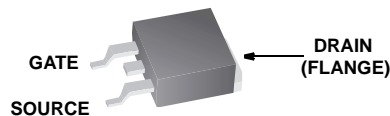
JEDEC STYLE TO-247



JEDEC TO-220AB



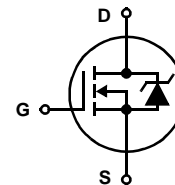
JEDEC TO-263AB



Features

- 75A, 55V
- Simulation Models
 - Temperature Compensated PSPICE® and SABER™ Models
 - SPICE and SABER Thermal Impedance Models Available on the WEB at: www.fairchildsemi.com
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- Related Literature
 - TB334, "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Product reliability information can be found at <http://www.fairchildsemi.com/products/discrete/reliability/index.html>
For severe environments, see our Automotive HUFA series.

All Fairchild semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

HUF75339G3, HUF75339P3, HUF75339S3S

Absolute Maximum Ratings $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

			UNITS
Drain to Source Voltage (Note 1)	V_{DSS}	55	V
Drain to Gate Voltage ($R_{GS} = 20\text{k}\Omega$) (Note 1)	V_{DGR}	55	V
Gate to Source Voltage	V_{GS}	± 20	V
Drain Current			
Continuous (Figure 2)	I_D	75	A
Pulsed Drain Current	I_{DM}	Figure 4	
Pulsed Avalanche Rating	E_{AS}	Figures 6, 14, 15	
Power Dissipation	P_D	200	W
Derate Above 25°C		1.35	$\text{W}/^{\circ}\text{C}$
Operating and Storage Temperature	T_J, T_{STG}	-55 to 175	$^{\circ}\text{C}$
Maximum Temperature for Soldering			
Leads at 0.063in (1.6mm) from Case for 10s	T_L	300	$^{\circ}\text{C}$
Package Body for 10s, See Techbrief 334	T_{pkg}	260	$^{\circ}\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- $T_J = 25^{\circ}\text{C}$ to 150°C .

Electrical Specifications $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
OFF STATE SPECIFICATIONS							
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ (Figure 11)	55	-	-	V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 50\text{V}, V_{GS} = 0\text{V}$	-	-	1	μA	
		$V_{DS} = 45\text{V}, V_{GS} = 0\text{V}, T_C = 150^{\circ}\text{C}$	-	-	250	μA	
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA	
ON STATE SPECIFICATIONS							
Gate to Source Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ (Figure 10)	2	-	4	V	
Drain to Source On Resistance	$r_{DS(ON)}$	$I_D = 75\text{A}, V_{GS} = 10\text{V}$ (Figure 9)	-	0.010	0.012	Ω	
THERMAL SPECIFICATIONS							
Thermal Resistance Junction to Case	$R_{\theta JC}$	(Figure 3)	-	-	0.74	$^{\circ}\text{C}/\text{W}$	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-247	-	-	30	$^{\circ}\text{C}/\text{W}$	
		TO-220, TO-263	-	-	62	$^{\circ}\text{C}/\text{W}$	
SWITCHING SPECIFICATIONS ($V_{GS} = 10\text{V}$)							
Turn-On Time	t_{ON}	$V_{DD} = 30\text{V}, I_D \equiv 75\text{A}, R_L = 0.4\Omega, V_{GS} = 10\text{V}, R_{GS} = 5.1\Omega$	-	-	110	ns	
Turn-On Delay Time	$t_{d(ON)}$		-	15	-	ns	
Rise Time	t_r		-	60	-	ns	
Turn-Off Delay Time	$t_{d(OFF)}$		-	20	-	ns	
Fall Time	t_f		-	25	-	ns	
Turn-Off Time	t_{OFF}		-	-	70	ns	
GATE CHARGE SPECIFICATIONS							
Total Gate Charge	$Q_{g(TOT)}$	$V_{GS} = 0\text{V}$ to 20V	$V_{DD} = 30\text{V}, I_D \equiv 75\text{A}, R_L = 0.4\Omega, I_g(\text{REF}) = 1.0\text{mA}$ (Figure 13)	-	110	130	nC
Gate Charge at 10V	$Q_{g(10)}$	$V_{GS} = 0\text{V}$ to 10V		-	60	75	nC
Threshold Gate Charge	$Q_{g(TH)}$	$V_{GS} = 0\text{V}$ to 2V		-	3.7	4.5	nC
Gate to Source Gate Charge	Q_{gs}			-	9	-	nC
Reverse Transfer Capacitance	Q_{gd}			-	23	-	nC

HUF75339G3, HUF75339P3, HUF75339S3S

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
CAPACITANCE SPECIFICATIONS						
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$ (Figure 12)	-	2000	-	pF
Output Capacitance	C_{OSS}		-	700	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	160	-	pF

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 75\text{A}$	-	-	1.25	V
Reverse Recovery Time	t_{rr}	$I_{SD} = 75\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	85	ns
Reverse Recovered Charge	Q_{RR}	$I_{SD} = 75\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	160	nC

Typical Performance Curves

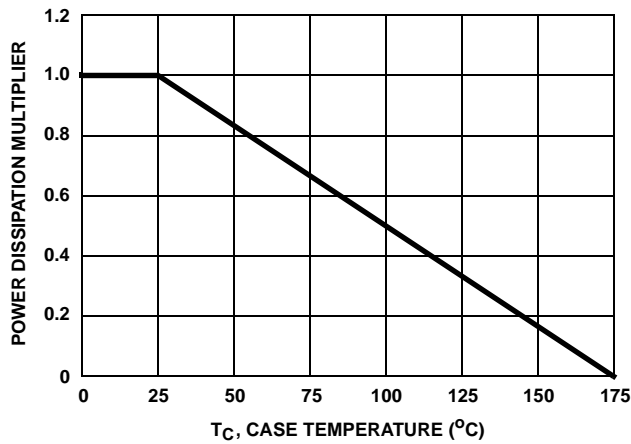


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

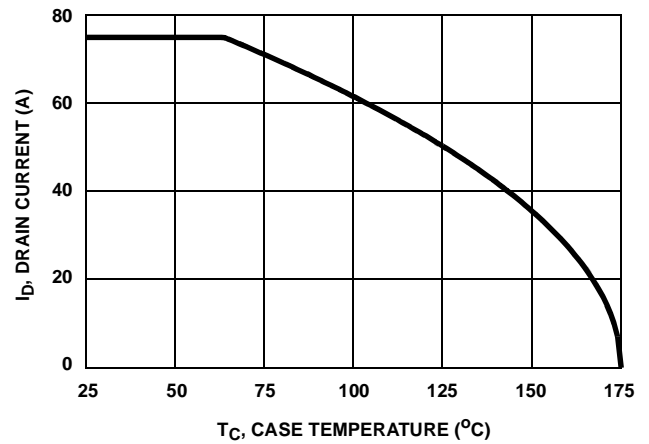


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

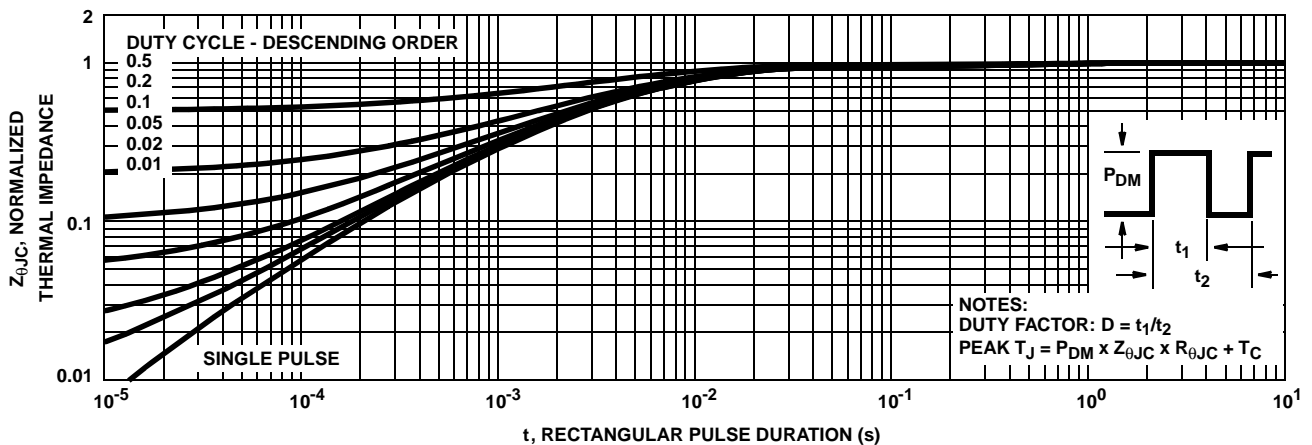


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

Typical Performance Curves (Continued)

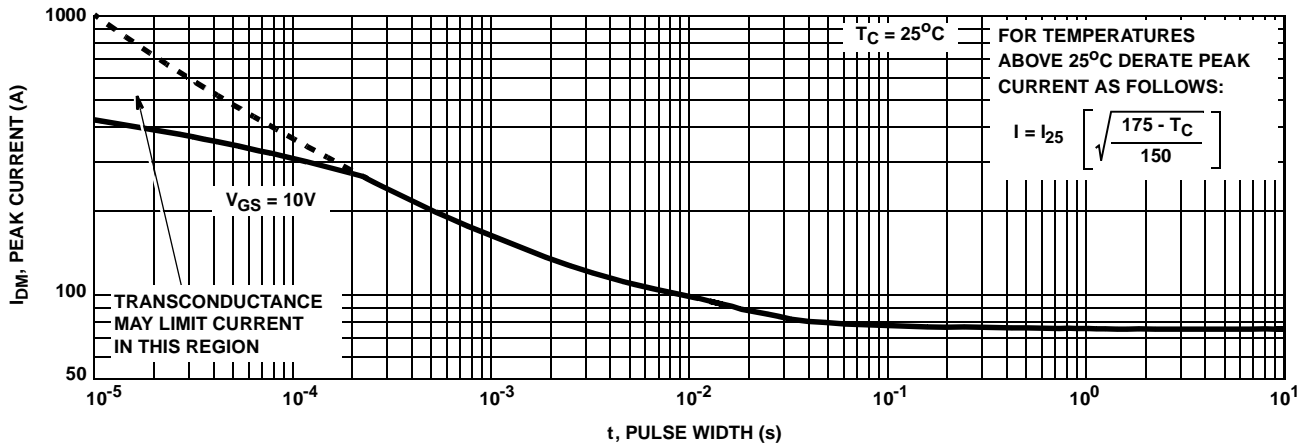


FIGURE 4. PEAK CURRENT CAPABILITY

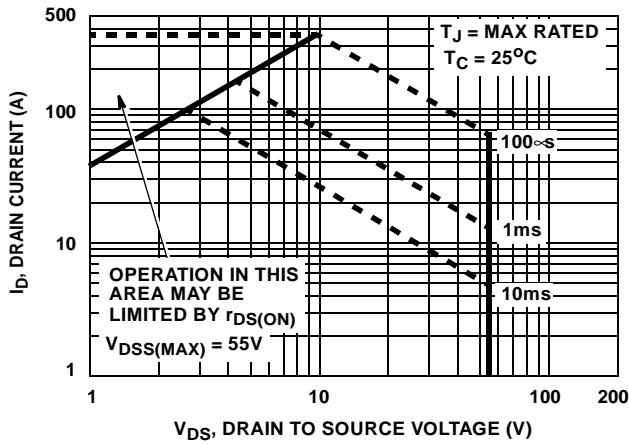
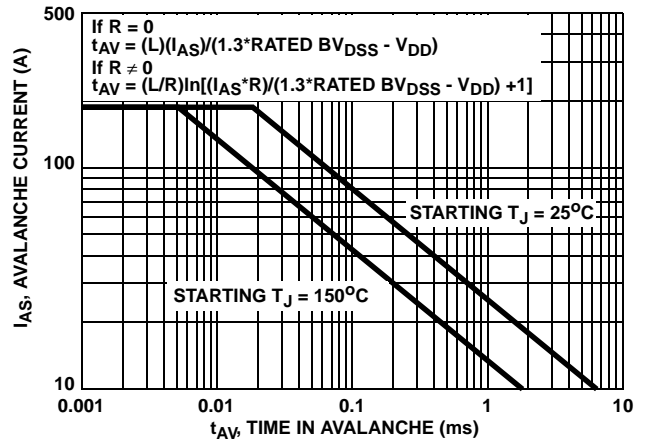


FIGURE 5. FORWARD BIAS SAFE OPERATING AREA



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

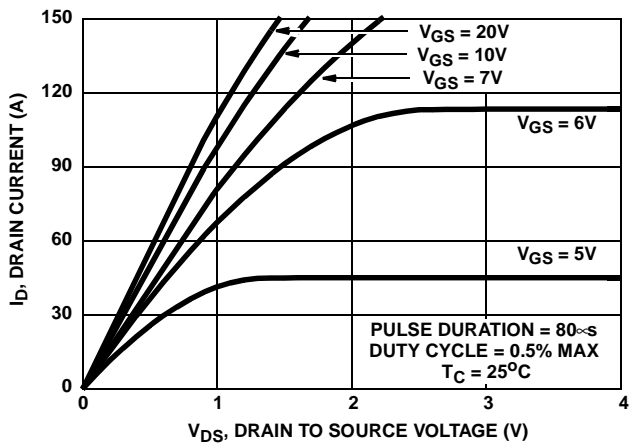


FIGURE 7. SATURATION CHARACTERISTICS

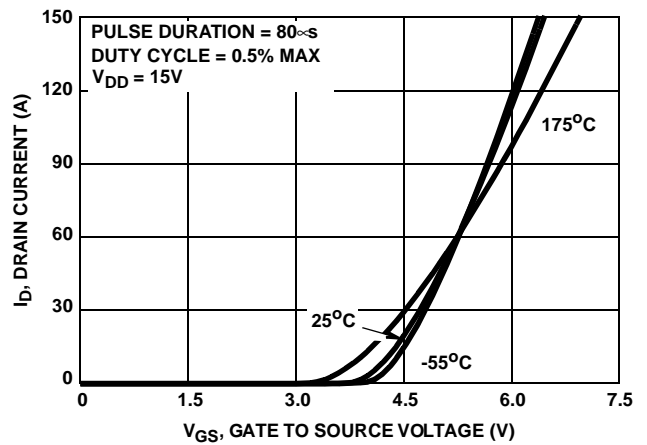


FIGURE 8. TRANSFER CHARACTERISTICS

Typical Performance Curves (Continued)

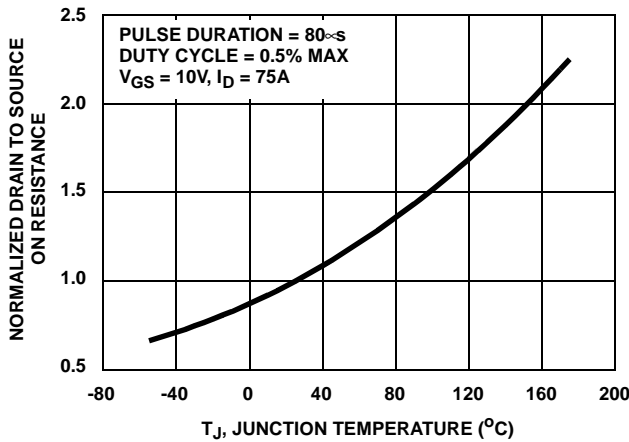


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

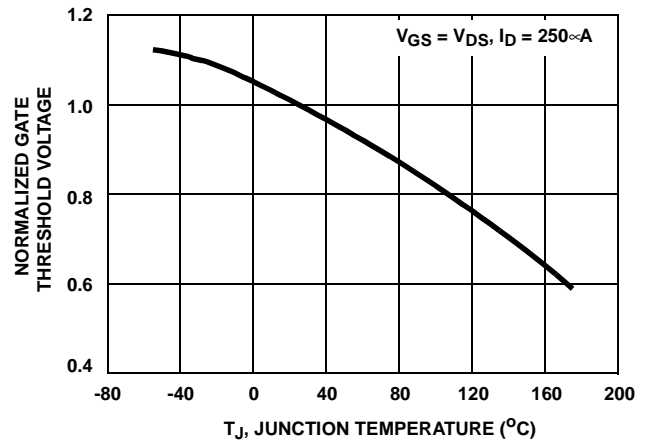


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

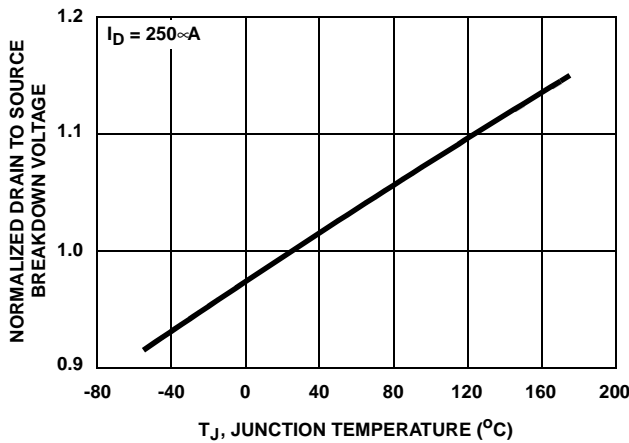


FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

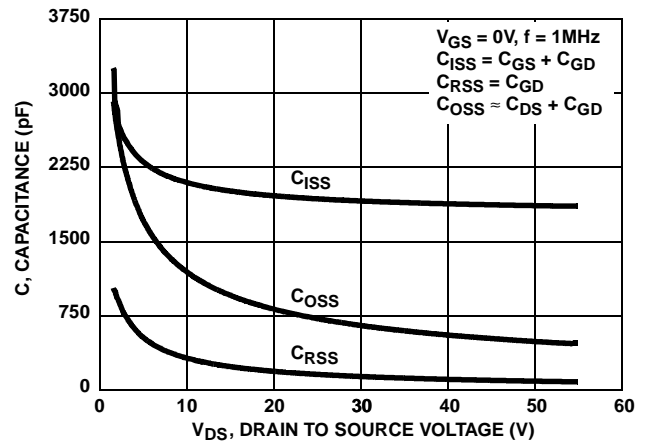
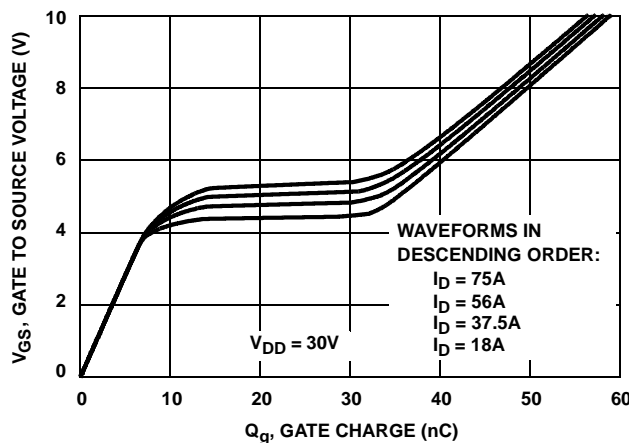


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 13. GATE CHARGE WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms

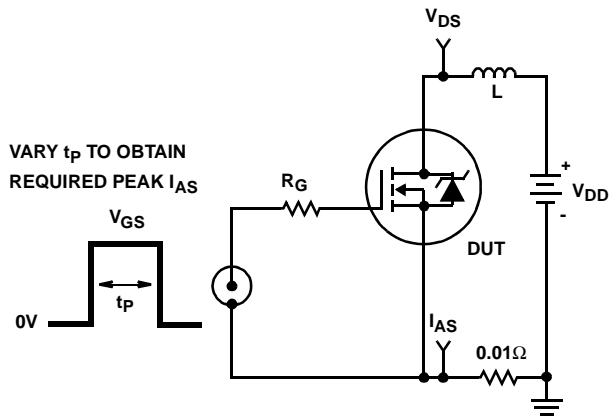


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

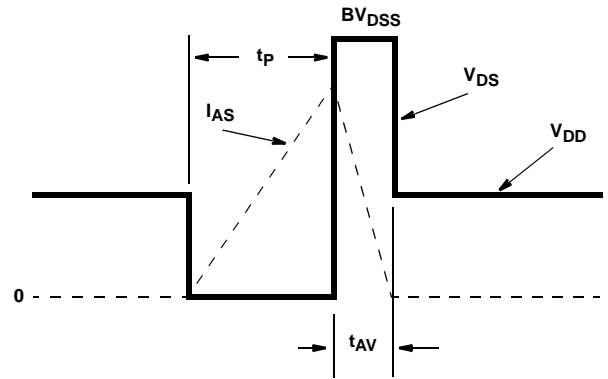


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

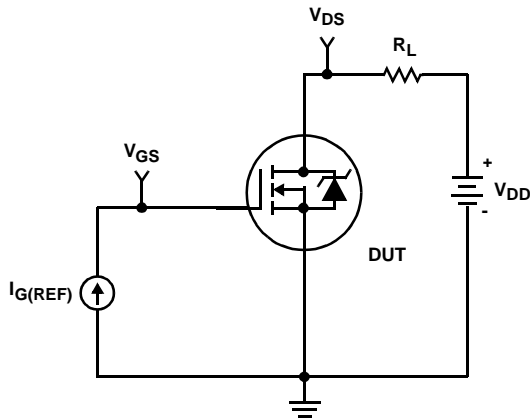


FIGURE 16. GATE CHARGE TEST CIRCUIT

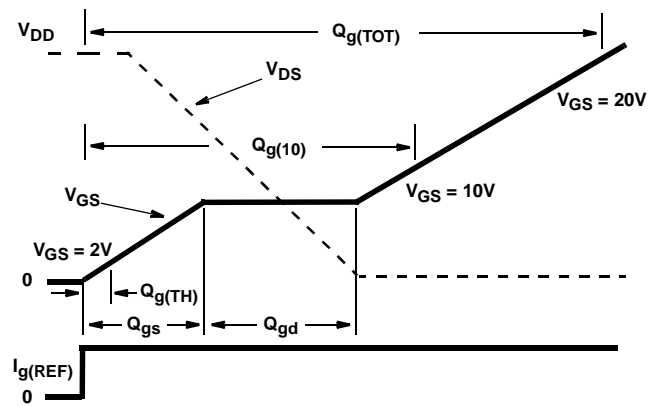


FIGURE 17. GATE CHARGE WAVEFORM

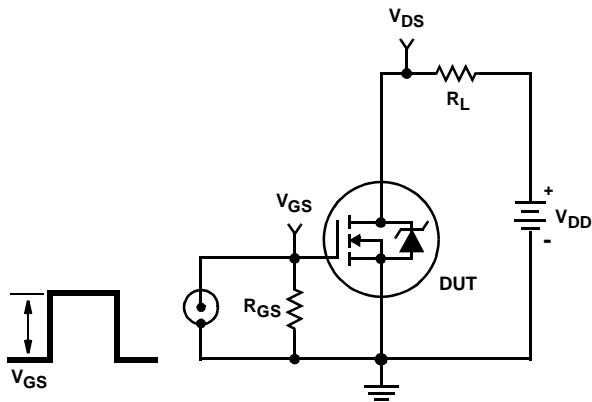


FIGURE 18. SWITCHING TIME TEST CIRCUIT

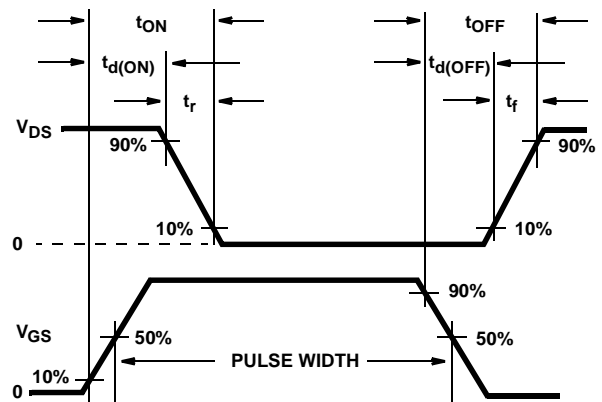


FIGURE 19. RESISTIVE SWITCHING WAVEFORMS

SPICE Thermal Model

REV 11 February 1999

HUF75339

CTHERM1 th 6 5.00e-3
 CTHERM2 6 5 1.90e-2
 CTHERM3 5 4 7.95e-3
 CTHERM4 4 3 9.00e-3
 CTHERM5 3 2 2.95e-2
 CTHERM6 2 tl 12.55

RTHERM1 th 6 5.04e-3
 RTHERM2 6 5 1.25e-2
 RTHERM3 5 4 3.54e-2
 RTHERM4 4 3 1.98e-1
 RTHERM5 3 2 2.99e-1
 RTHERM6 2 tl 3.97e-2

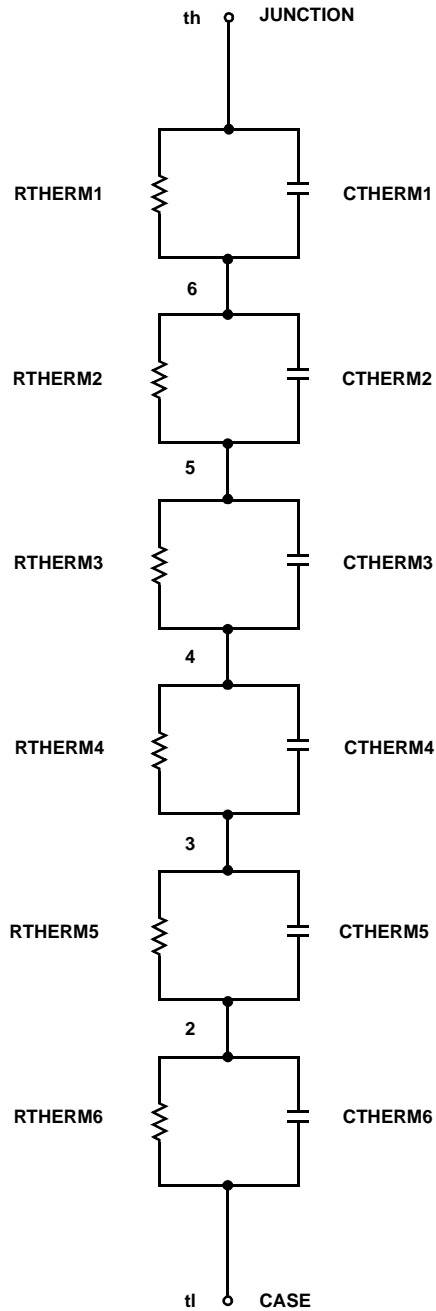
SABER Thermal Model

SABER thermal model HUF75339

template thermal_model th tl
 thermal_c th, tl

```
{
ctherm.ctherm1 th 6 = 5.00e-3
ctherm.ctherm2 6 5 = 1.90e-2
ctherm.ctherm3 5 4 = 7.95e-3
ctherm.ctherm4 4 3 = 9.00e-3
ctherm.ctherm5 3 2 = 2.95e-2
ctherm.ctherm6 2 tl = 12.55
```



```
rtherm.rtherm1 th 6 = 5.04e-3
rtherm.rtherm2 6 5 = 1.25e-2
rtherm.rtherm3 5 4 = 3.54e-2
rtherm.rtherm4 4 3 = 1.98e-1
rtherm.rtherm5 3 2 = 2.99e-1
rtherm.rtherm6 2 tl = 3.97e-2
}
```





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